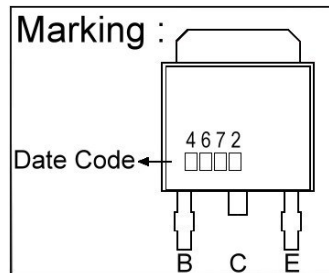
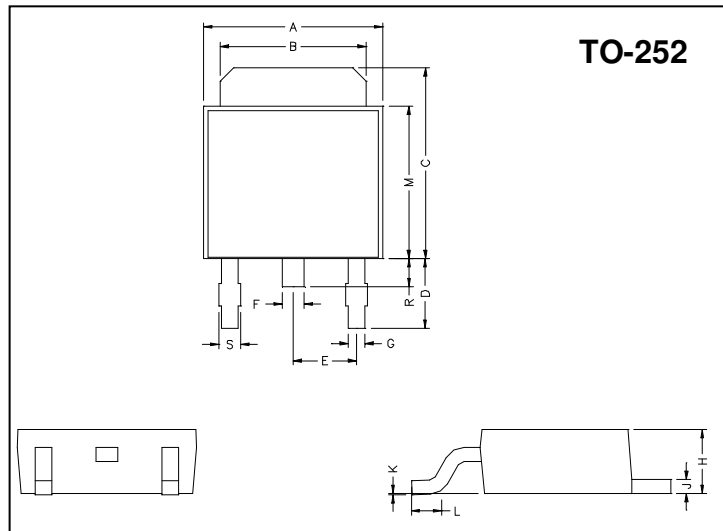


GJ4672**NPN EPITAXIAL SILICON TRANSISTOR****Description**

The GJ4672 is designed for low frequency amplifier applications.

Features

- Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$
- Excellent DC current gain characteristics

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings ($T_A = 25^\circ C$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse PW=10ms)	I_C	5	A
Total Device Dissipation ($T_A = 25^\circ C$)	P_D	1.5	W
Total Device Dissipation ($T_C = 25^\circ C$)	P_D	10	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

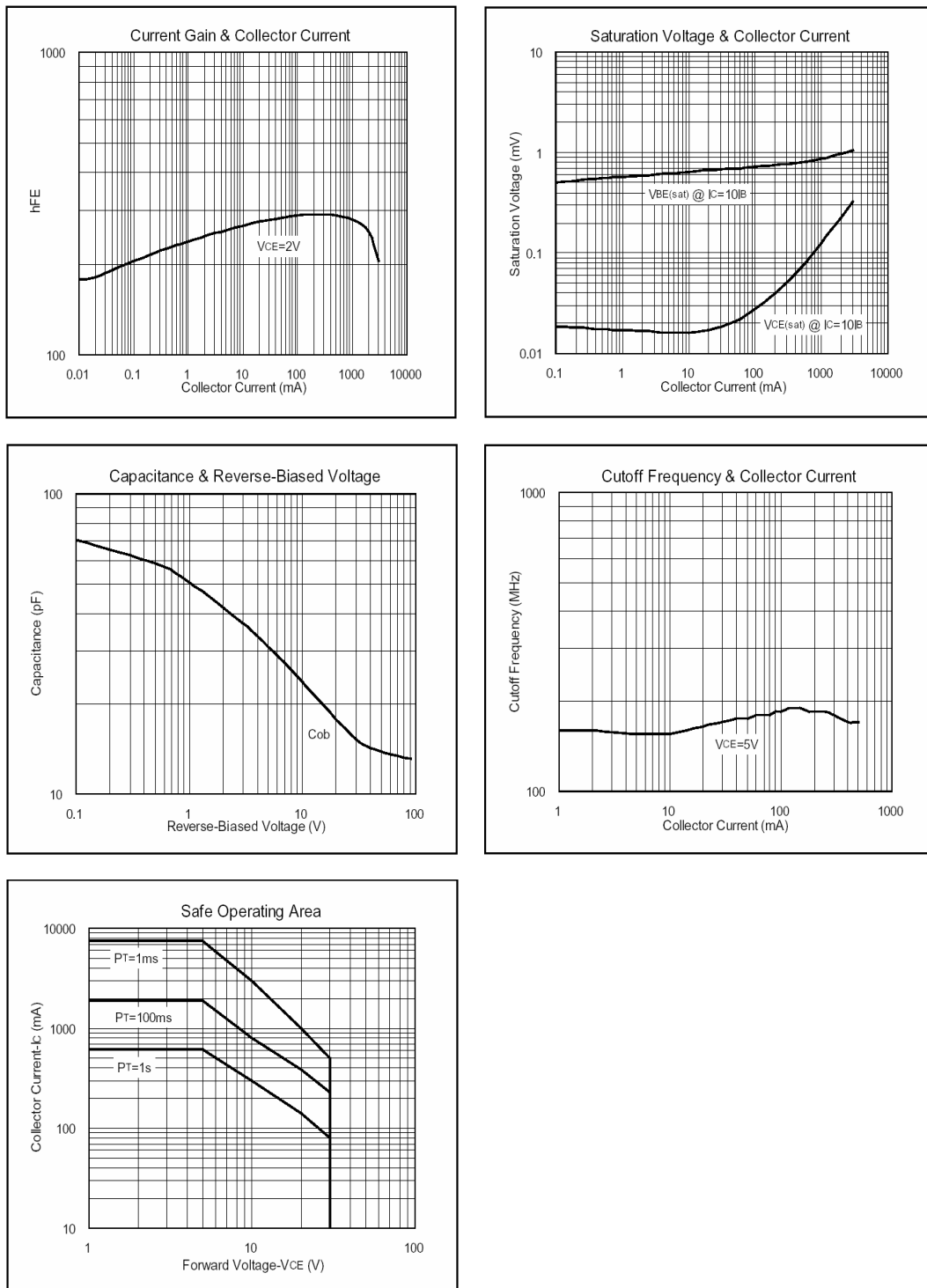
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	60	-	-	V	$I_C = 50\mu A, I_E = 0$
BV_{CEO}	50	-	-	V	$I_C = 1mA, I_B = 0$
BV_{EBO}	6	-	-	V	$I_E = 50\mu A, I_C = 0$
I_{CBO}	-	-	100	nA	$V_{CB} = 60V, I_E = 0$
I_{EBO}	-	-	100	nA	$V_{EB} = 5V, I_C = 0$
* $V_{CE(sat)}$	-	0.1	0.35	V	$I_C = 1A, I_B = 50mA$
* h_{FE}	120	-	400		$V_{CE} = 2V, I_C = 500mA$
f _T	-	210	-	MHz	$V_{CE} = 2V, I_E = 500mA, f = 100MHz$
C _{ob}	-	25	-	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	A	B
Range	120 ~ 240	200 ~ 400

Characteristics Curve



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